

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A semiconductor module comprising:

an insulating base material provided with a conductor circuit;

a semiconductor element formed on said insulating base material; and

an insulator disposed in contact with said insulating base material and said semiconductor element,

wherein said insulating base material is provided with minute projections formed on a surface thereof that is in contact with said insulator, the minute projections being a part of the insulating base material and comprising projections and recesses on a portion of the insulating base material being in contact with the insulator ~~by forming projections and recesses on the insulating base material~~, and

said minute projections include a plurality of projections of 1 nm to 20 nm in average diameter and formed in a number density of not less than $0.5 \times 10^3 \mu\text{m}^{-2}$.
2. (Previously Presented) The semiconductor module as set forth in Claim 1, wherein said insulator is a sealing resin for sealing the semiconductor element therein.
3. (Original) The semiconductor module as set forth in Claim 1, wherein said insulator is an adhesive provided between said semiconductor element and said insulating base material.

4. (Original) The semiconductor module as set forth in Claim 1, wherein a plurality of crater-shaped recesses is formed on a surface of said insulating base material that is in contact with said insulator.

5. (Original) The semiconductor module as set forth in Claim 4, wherein a diameter of said crater-shaped recess is in a range of 0.1 μm to 1 μm .

6-10. (Cancelled)

11. (Original) The semiconductor module as set forth in Claim 1, wherein said semiconductor element is a bare chip and said insulator is constituted essentially of a sealing resin for sealing said bare chip therein.

12-14. (Cancelled)

15. (Currently Amended) A module comprising:
a base material;
an element formed on said base material; and
an insulator disposed in contact with said base material and said element,
wherein said base material is provided with minute projections formed on a surface thereof that is in contact with said insulator, the minute projections being a part of the base material and comprising projections and recesses on a portion of the base material being in

contact with the insulator ~~by forming projections and recesses on the insulating base material,~~
and

said minute projections include a plurality of projections of 1 nm to 20 nm in average diameter and formed in a number density of not less than $0.5 \times 10^3 \mu\text{m}^{-2}$.

16. (Original) The module as set forth in Claim 15, wherein a plurality of crater-shaped recesses is formed on a surface of said base material that is in contact with said insulator.

17-28. (Cancelled)

29. (Currently Amended) A semiconductor module comprising:
an insulating base material provided with a conductor circuit;
a semiconductor element formed on said insulating base material; and
an insulator disposed in contact with said insulating base material and said semiconductor element;

wherein said insulating base material is provided with minute projections on a surface thereof that is in contact with said insulator, the minute projections being a part of the insulating base material and comprising projections and recesses on a portion of the insulating base material being in contact with the insulator, and

said minute projections include a plurality of projections of 1 nm to 20 nm in average diameter.

30. (Previously Presented) The semiconductor module as set forth in Claim 29, wherein said insulator is a sealing resin for sealing the semiconductor element therein.

31. (Previously Presented) The semiconductor module as set forth in Claim 29, wherein said insulator is an adhesive provided between said semiconductor element and said insulating base material.

32. (Previously Presented) The semiconductor module as set forth in Claim 29, wherein a plurality of crater-shaped recesses is formed on a surface of said insulating base material that is in contact with said insulator.

33. (Previously Presented) The semiconductor module as set forth in Claim 32, wherein a diameter of said crater-shaped recess is in a range of $0.1\ \mu\text{m}$ to $1\ \mu\text{m}$.

34. (Previously Presented) The semiconductor module as set forth in Claim 29, wherein said minute projections include a plurality of projections formed in a number density of not less than $0.5 \times 10^3\ \mu\text{m}^{-2}$.

35. (Previously Presented) The semiconductor module as set forth in Claim 29, wherein said semiconductor element is a bare chip and said insulator is constituted essentially of a sealing resin for sealing said bare chip therein.